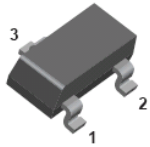


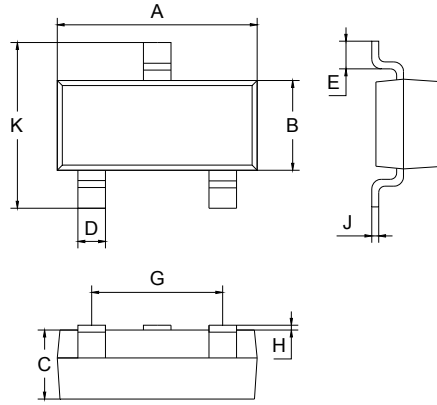


### Features

- For general AF applications
- Complementary NPN type available BC817
- High collector current
- High current gain
- Low collector-emitter saturation voltage



1. BASE  
2. EMITTER  
3. COLLECTOR



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

### Ordering Information

Type No.	Marking	Package Code
<b>BC807-16</b>	<b>5A</b>	<b>SOT-23</b>
<b>BC807-25</b>	<b>5B</b>	<b>SOT-23</b>
<b>BC807-40</b>	<b>5C</b>	<b>SOT-23</b>

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

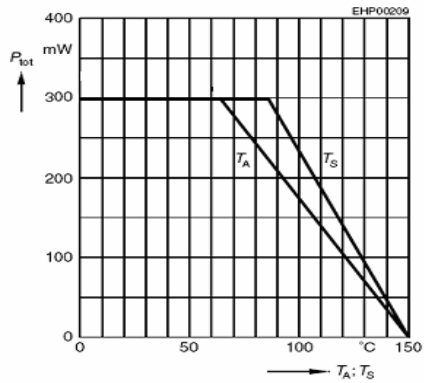
Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector- Base Voltage	-50	V
V <sub>CEO</sub>	Collector- Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter- Base Voltage	-5	V
I <sub>C</sub>	Collector Current - Continuous	-500	mA
P <sub>D</sub>	Total Device Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient	417	°C/W
T <sub>j</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55 to +150	°C



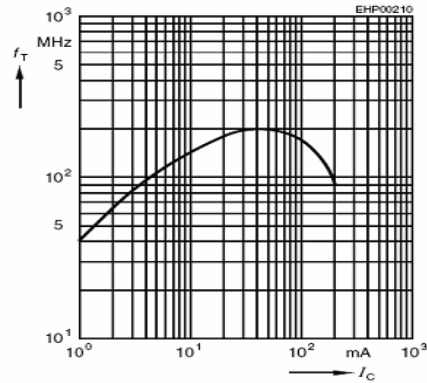
**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector- base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-50			V
Collector- emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-45			V
Emitter- base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			$\mu V$
Collector cut-off current	$I_{CBO}$	$V_{CB} = -25V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{CE} = -4V, I_C = 0$			-0.1	$\mu A$
DC current gain						
	807- 16	$V_{CE} = -1V, I_C = -100mA$	100	160	250	
	807-25		160	250	400	
	807-40		250	350	600	
DC current gain						
	807- 16	$V_{CE} = -1V, I_C = -300mA$	60			
	807-25		100			
	807-40		170			
Collector- emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.7	V
Base- emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Output capacitance	$C_{obo}$	$V_{CB} = -10V, f = 1.0MHz$			10	pF
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$		200		MHz

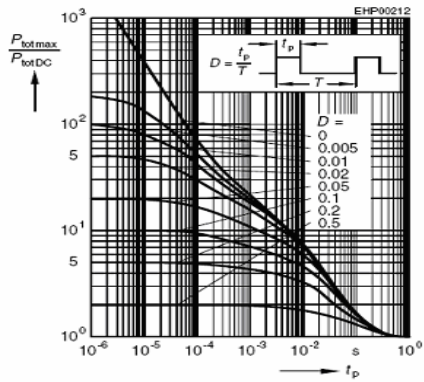
**Total power dissipation  $P_{tot} = f(T_A^*; T_S)$**   
\* Package mounted on epoxy



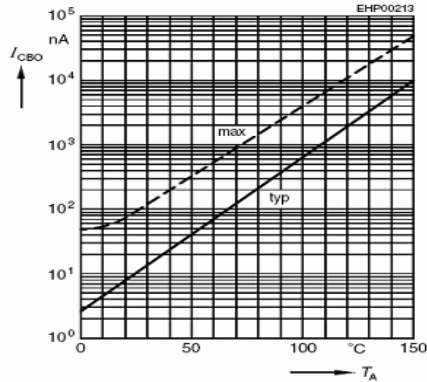
**Transition frequency  $f_T = f(I_C)$**   
 $V_{CE} = 5V$



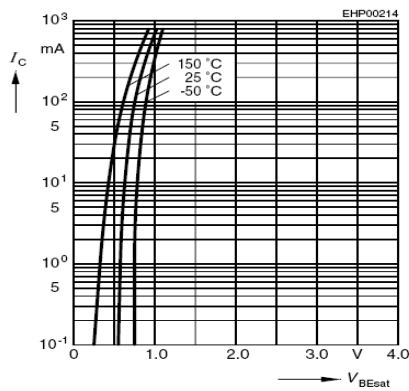
**Permissible pulse load**  
 $P_{totmax} / P_{totDC} = f(t_p)$



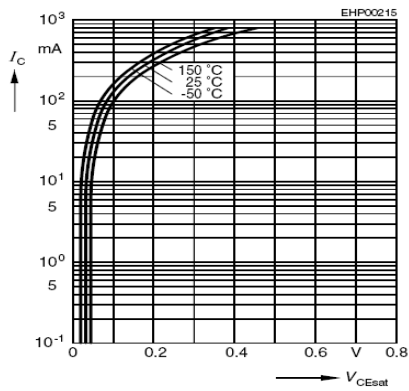
**Collector cutoff current  $I_{CBO} = f(T_A)$**   
 $V_{CBO} = 25V$



**Base-emitter saturation voltage**  
 $I_C = f(V_{BEsat}), h_{FE} = 10$



**Collector-emitter saturation voltage**  
 $I_C = f(V_{CEsat}), h_{FE} = 10$



Device	Package	Shipping
BC807-16/-25/-40	SOT-23	3000/Tape&Reel